ABSTRACT OF THE DISCLOSURE

Composite TiO_2/Ta_2O_5 films by in-situ sequential CVD deposition are presented. for a storage capacitor of a three-dimensional cell in DRAM applications. The capacitor with the $Ta_2O_5/TiO_2/Ta_2O_5$ alternating layer structure has comparable leakage current density and higher capacitance per unit area as compared to a capacitor with Ta_2O_5 and TiO_2 single layer structures.

Fig. 4.

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